

Amendments to the Claims:

The listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claims 1 – 10 (cancelled)

Claim 11 (currently amended) A kind of non-volatile memory structure, including:
a base;

a gate dielectric layer on the base, the gate dielectric layer with an increased electron trapping density has at least one kind of hetero element, other than Nitrogen, ~~to increase the electron trapping density~~;

a gate electrode layer on the top of the said gate dielectric layer; and

a source/drain electrodes at the base on both sides of the said gate dielectric layer.

Claim 12 (previously presented) The non-volatile memory structure as claimed in claim 11, where the gate dielectric layer turns from bottom to the top including a first oxide layer, a nitride layer and a second oxide layer.

Claim 13 (previously presented) The non-volatile memory structure as claimed in claim 11, where the hetero elements used are any one within Germanium (Ge), Silicon (Si), Oxygen (O₂), Oxygen (O) separately or multiple mixture therefrom.

Claim 14 (previously presented) The non-volatile memory structure as claimed in claim 11, where the hetero elements used are compounds of Germanium (Ge), Silicon (Si), Oxygen (O).

Claim 15 (new) The non-volatile memory structure as claimed in claim 11, where the hetero elements used are compounds of Germanium (Ge).

Claim 16 (new) The non-volatile memory structure as claimed in claim 11, where the hetero elements used are compounds of Oxygen (O).